Dual N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
40	0.027 at V_{GS} = 10 V	6.0	9.6
	0.032 at V_{GS} = 4.5 V	4.8	

FEATURES

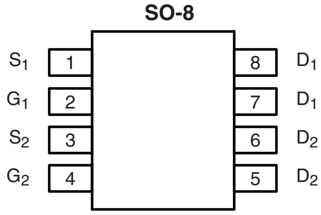
- **Halogen-free According to IEC 61249-2-21 Available**
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

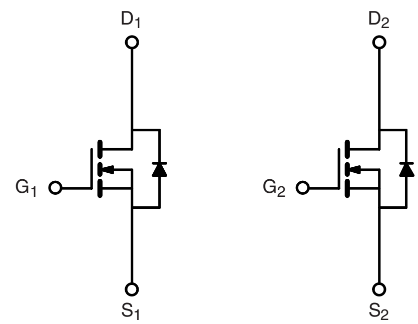
- CCFL Inverter

SO-8



Top View

Ordering Information: Si4910DY-T1-E3 (Lead (Pb)-free)
Si4910DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET   N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 16	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	7.6	A
	T_C = 70 °C		6.0	
	T_A = 25 °C		6.0[b, c]	
	T_A = 70 °C		4.8[b, c]	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	20	
Source-Drain Current Diode Current	T_C = 25 °C	I_S	2.6	
	T_A = 25 °C		1.6[b, c]	
Pulsed Source-Drain Current		I_{SM}	20	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	10	
Single Pulse Avalanche Energy		E_{AS}	5	
Maximum Power Dissipation	T_C = 25 °C	P_D	3.1	W
	T_C = 70 °C		2	
	T_A = 25 °C		2[b, c]	
	T_A = 70 °C		1.28[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	49	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady-State	R_{thJF}	30	40	

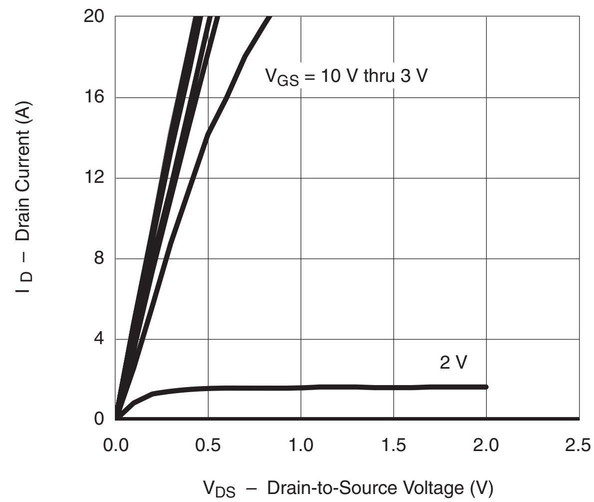
Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 120 °C/W.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**[a]	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	40			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		37		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D= 250 µA	0.6		2.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			1	µA
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 6 A		0.022	0.027	Ω
		V_{GS} = 4.5 V, I_D = 4.8 A		0.026	0.032	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 6 A		20		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, I_D = 1 MHz		855		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			65		
Total Gate Charge	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 5 A		21	32	nC
		V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 5 A		9.6	14.5	
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			3.2		
Gate Resistance	R_g	f = 1 MHz		2.5	3.8	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 4 Ω $I_D \cong$ 5 A, V_{GEN} = 10 V, R_g = 1 Ω		6	12	ns
Rise Time	t_r			11	20	
Turn-Off Delay Time	$t_{d(off)}$			24	36	
Fall Time	t_f			6	12	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L =4 Ω $I_D \cong$ 5 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	20	
Rise Time	t_r			60	90	
Turn-Off Delay Time	$t_{d(off)}$			22	33	
Fall Time	t_f			5	10	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			2.6	A
Pulse Diode Forward Current[a]	I_{SM}				20	
Body Diode Voltage	V_{SD}	I_S = 1.5 A		0.73	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 5 A, dI/dt = 100 A/µs, T_J = 25 °C		26	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			21	32	nC
Reverse Recovery Fall Time	t_a			13		ns
Reverse Recovery Rise Time	t_b			13		

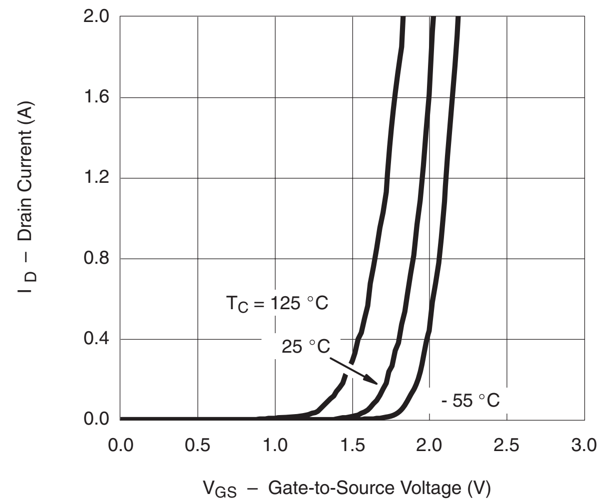
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

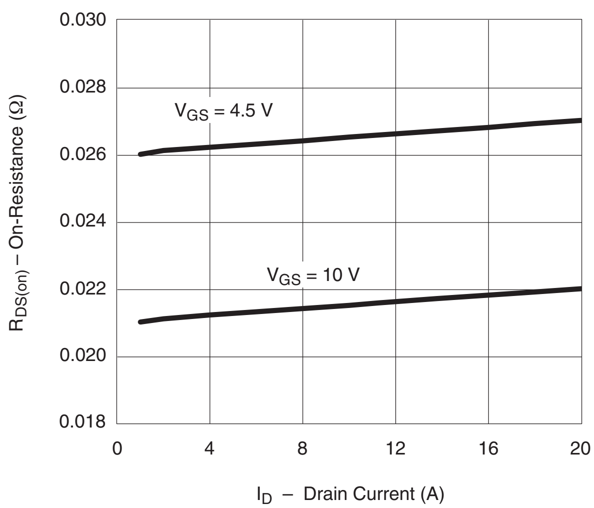
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



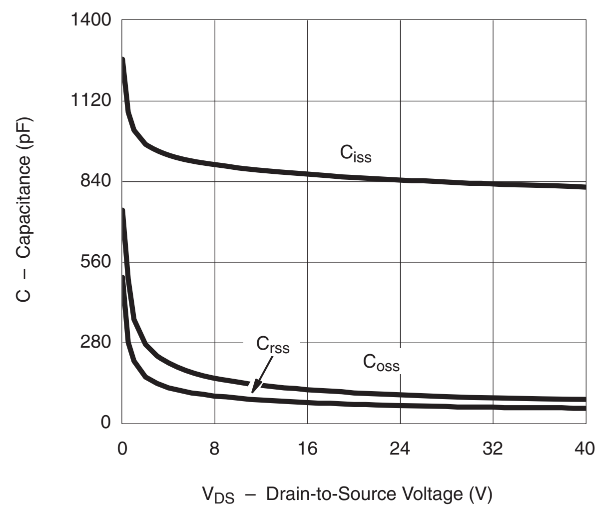
Output Characteristics



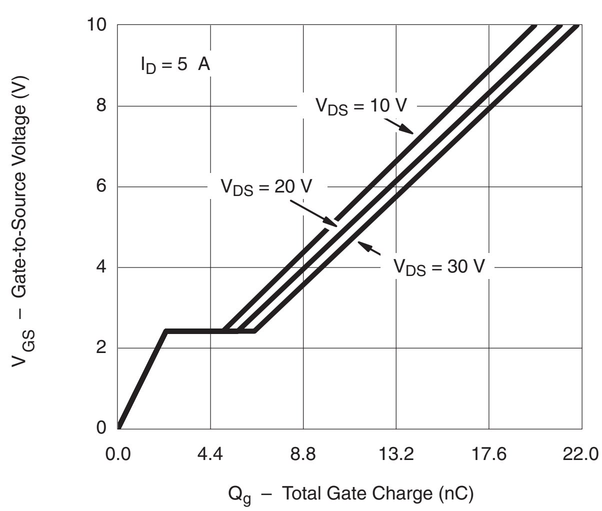
Transfer Characteristics



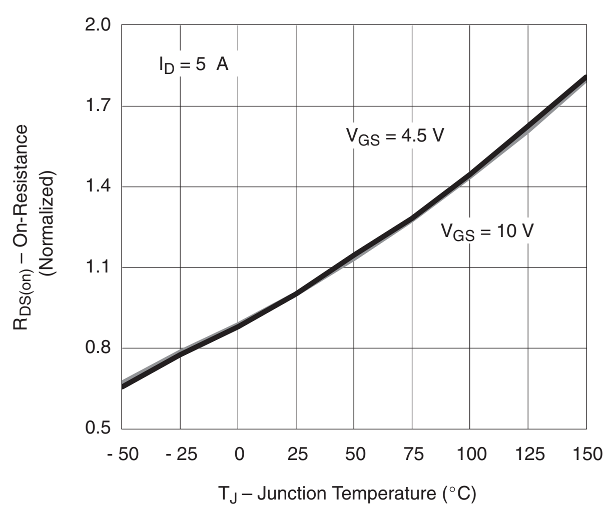
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

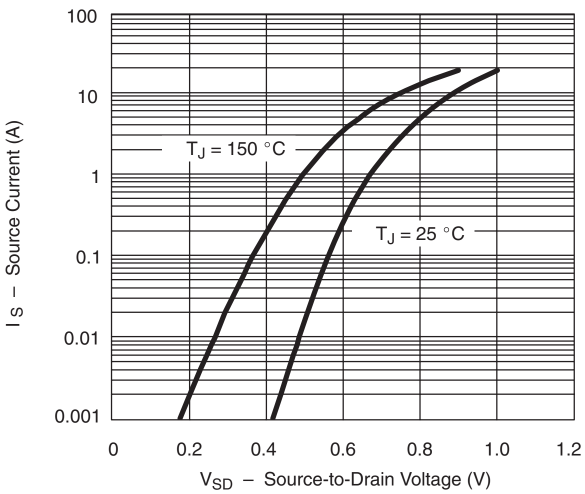


Gate Charge

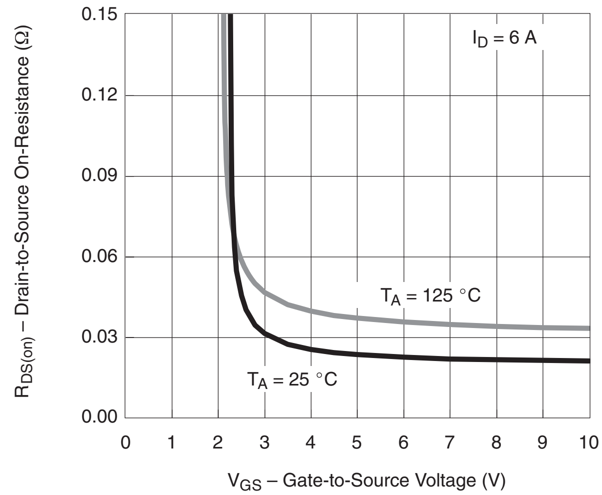


On-Resistance vs. Junction Temperature

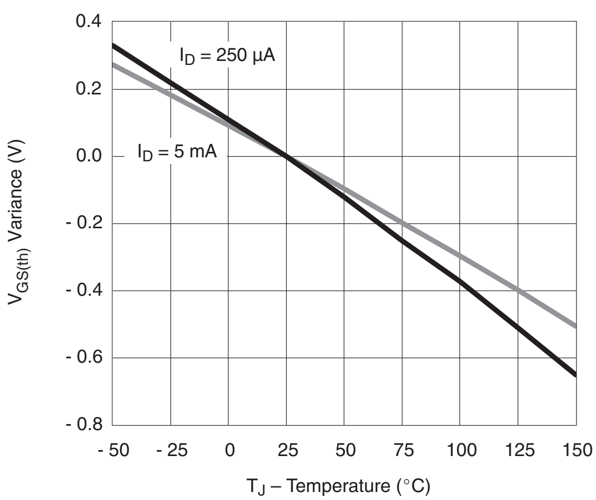
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



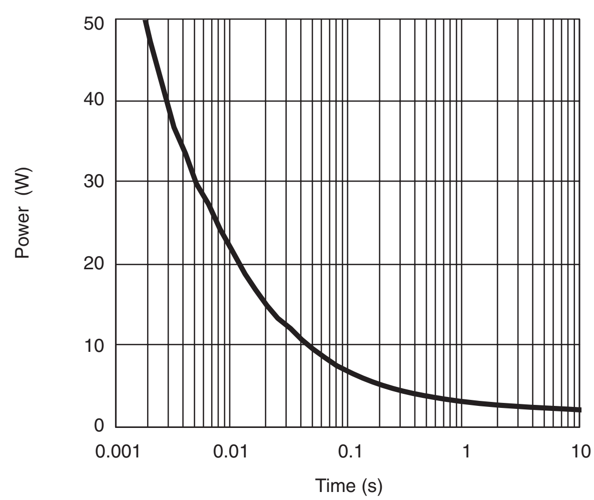
Source-Drain Diode Forward Voltage



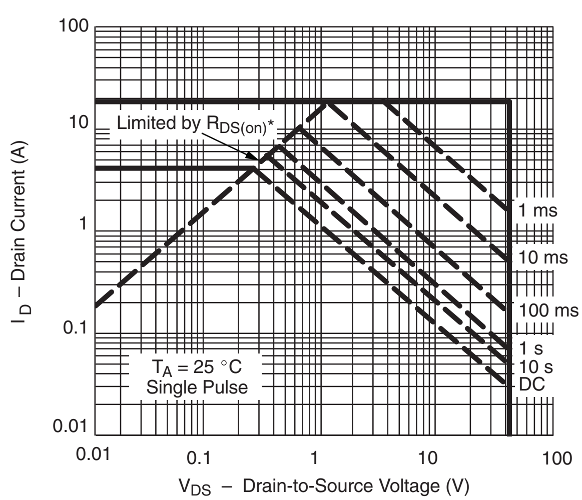
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



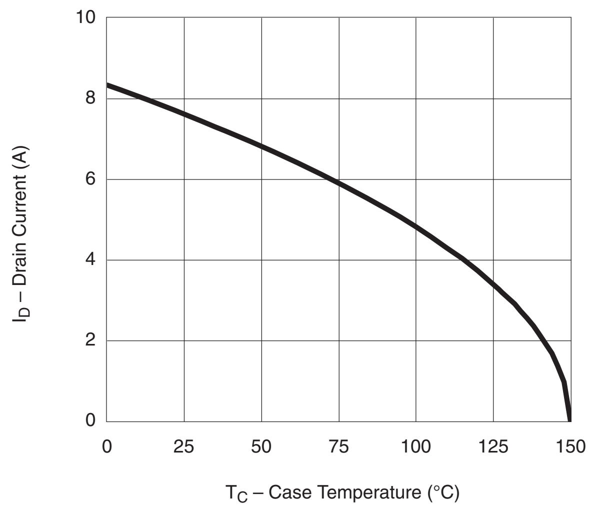
Single Pulse Power, Junction-to-Ambient



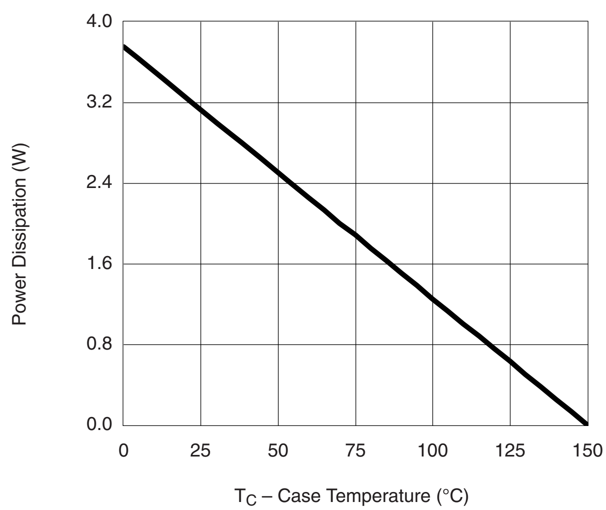
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

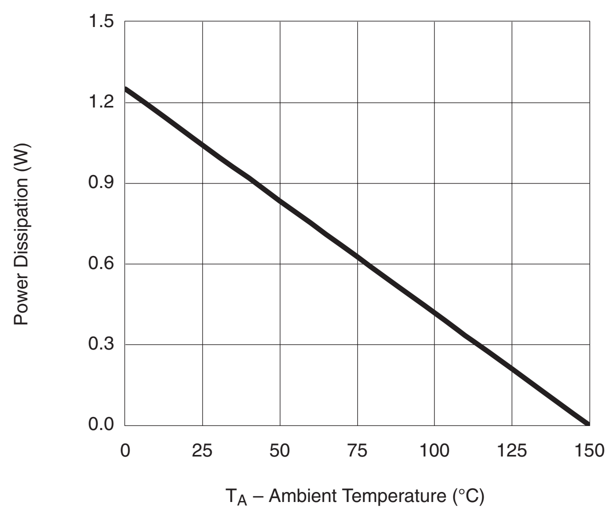
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



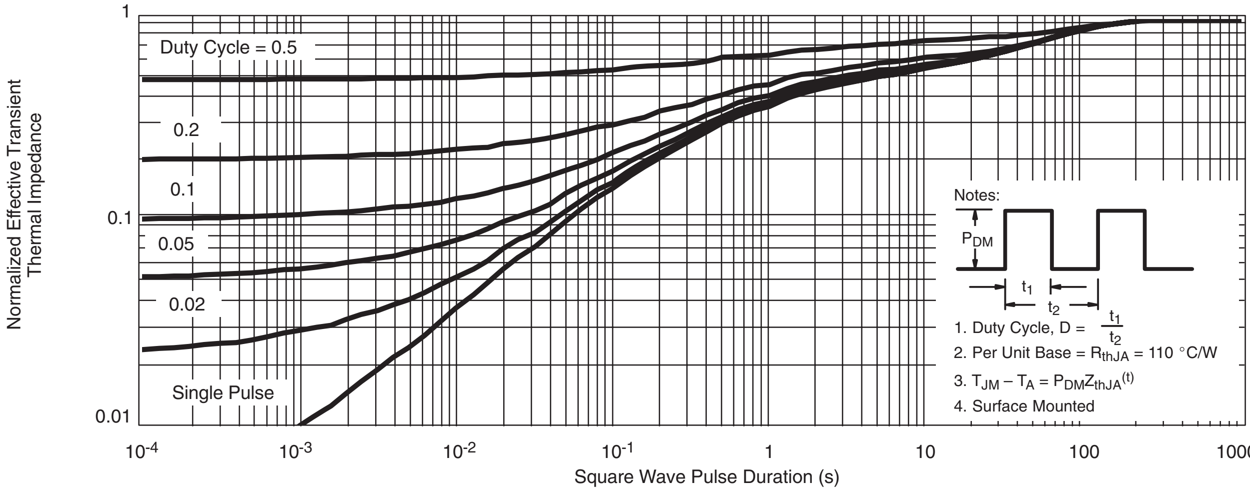
Power Derating, Junction-to-Foot



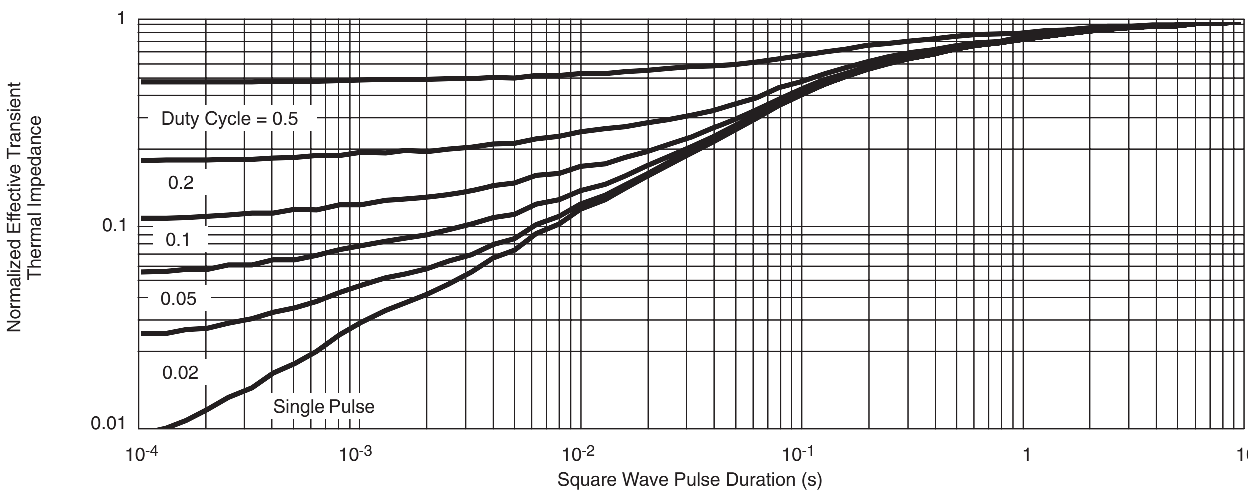
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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